Darlington Amplifier Transistors

NPN Silicon

MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CES}	30	Vdc
Collector - Base Voltage	V _{CBO}	30	Vdc
Emitter - Base Voltage	V _{EBO}	10	Vdc
Collector Current - Continuous	Ic	300	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

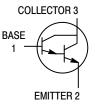


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SOT-23 (TO-236) CASE 318 STYLE 6



MARKING DIAGRAM



1x = Device Code

x = M for MMBTA13LT1G, SMMBTA13LT1G x = N for MMBTA14LT1G,

SMMBTA14LT1G, T3G

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBTA13LT1G, SMMBTA13LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA14LT1G, SMMBTA14LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA14LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage ($I_C = 100 \mu Adc, V_{BE} = 0$)	V _(BR) CES	30	_	Vdc		
Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)	Ісво	-	100	nAdc		
Emitter Cutoff Current $(V_{EB} = 10 \text{ Vdc}, I_C = 0)$	I _{EBO}	-	100	nAdc		
ON CHARACTERISTICS (Note 3)						
DC Current Gain $ \begin{aligned} &(I_C=10 \text{ mAdc, V}_{CE}=5.0 \text{ Vdc})\\ &\text{MMBTA13, SMMBTA13}\\ &\text{MMBTA14, SMMBTA14}\\ &(I_C=100 \text{ mAdc, V}_{CE}=5.0 \text{ Vdc})\\ &\text{MMBTA13, SMMBTA13}\\ &\text{MMBTA14, SMMBTA13}\\ &\text{MMBTA14, SMMBTA14} \end{aligned} $	h _{FE}	5000 10,000 10,000 20,000	- - -	-		
Collector – Emitter Saturation Voltage ($I_C = 100 \text{ mAdc}$, $I_B = 0.1 \text{ mAdc}$)	V _{CE(sat)}	_	1.5	Vdc		
Base – Emitter On Voltage (I _C = 100 mAdc, V _{CE} = 5.0 Vdc)	V _{BE}	_	2.0	Vdc		
SMALL-SIGNAL CHARACTERISTICS	<u>.</u>					
Current – Gain – Bandwidth Product (Note 4) (I _C = 10 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	125	-	MHz		

^{3.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

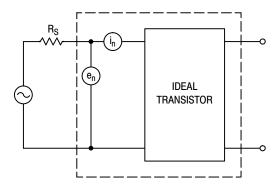


Figure 1. Transistor Noise Model

^{4.} $f_T = |h_{fe}| \bullet f_{test}$.

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

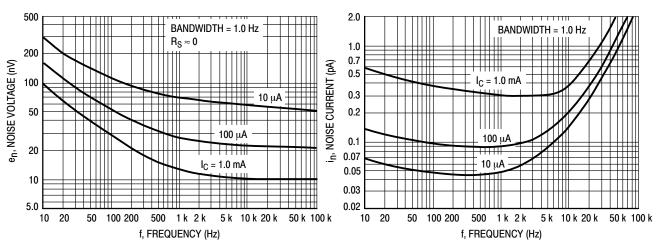


Figure 2. Noise Voltage

Figure 3. Noise Current

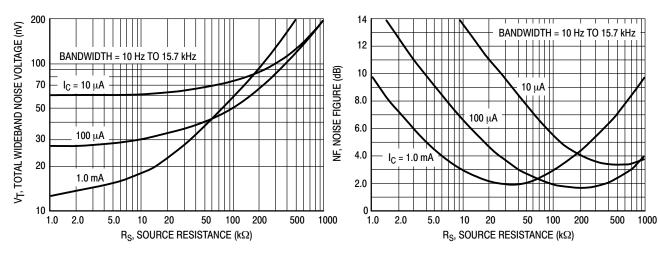


Figure 4. Total Wideband Noise Voltage

Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

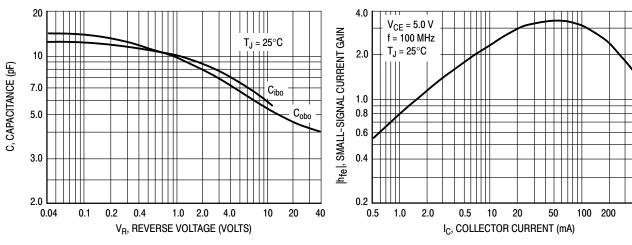


Figure 6. Capacitance

Figure 7. High Frequency Current Gain

500

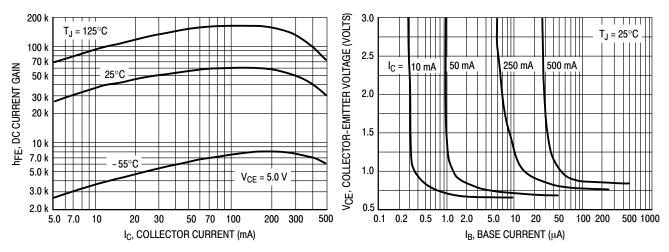


Figure 8. DC Current Gain

Figure 9. Collector Saturation Region

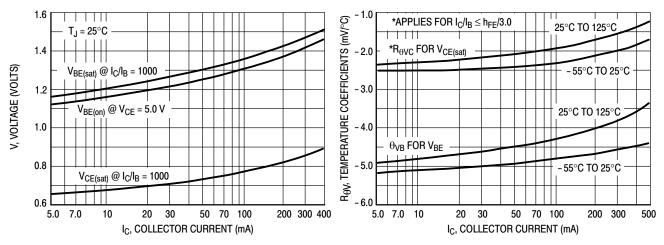


Figure 10. "On" Voltages

Figure 11. Temperature Coefficients

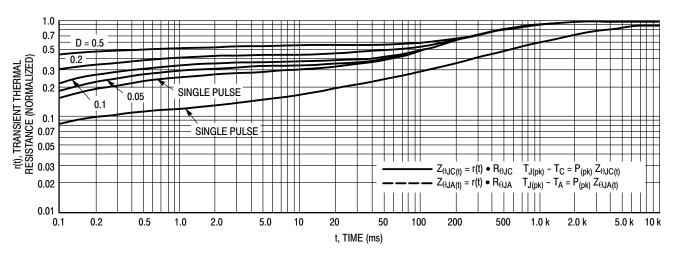


Figure 12. Thermal Response

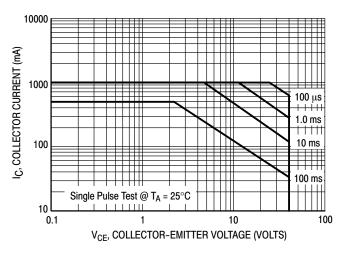
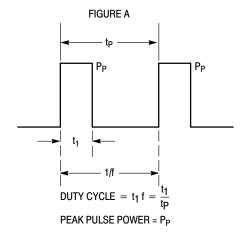


Figure 13. Active Region Safe Operating Area



Design Note: Use of Transient Thermal Resistance Data

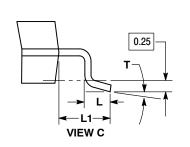


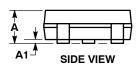
SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

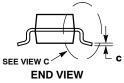
DATE 30 JAN 2018

SCALE 4:1 D - 3X b

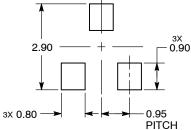
TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

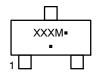
NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	3. GATE	CATHODE-ANODE	ANODE	3. GATE	ANODE

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
CATHODE	CATHODE	2. ANODE	CATHODE	2. ANODE	ANODE
ANODE	CATHODE	CATHODE	ANODE	CATHODE-ANOD	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
SOURCE	OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	NO CONNECTION

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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